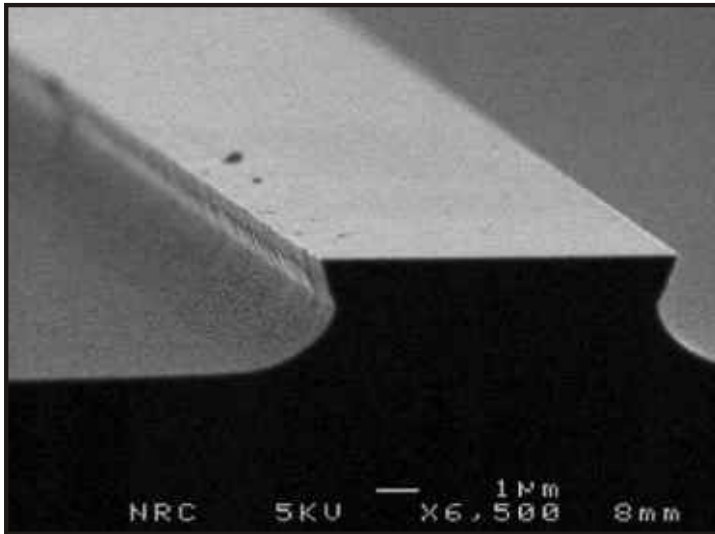
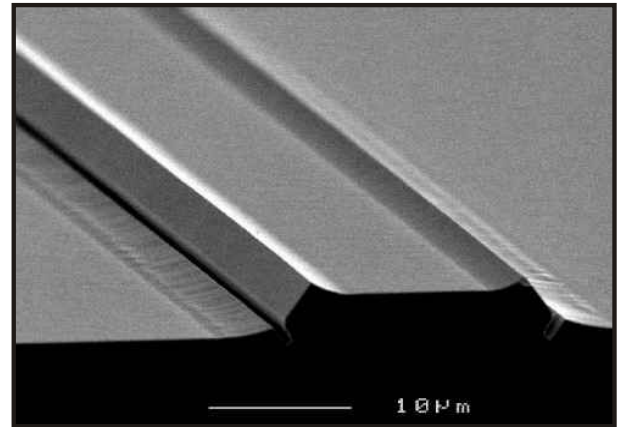


Ionfab Data

InGaAs/ InP CAIBE: deep undercut mesas



Courtesy of National Research Council, Ottawa
(Dr B. Lamontagne, Dr P. J. Poole)

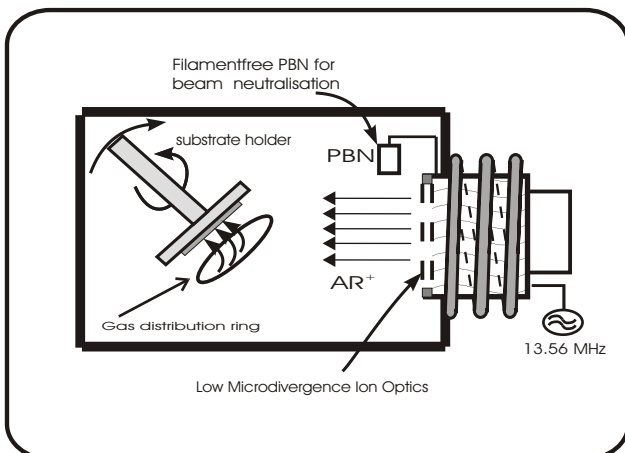


left SEM:
image of the patterned substrate
before growth: The etched ridge is in
the (011) direction.

right SEM:
picture of a layer grown on the patterned
substrate showing the (111) B facets:
These were measured to be atomically flat
by AFM.

Technology:

- Etch Mode: CAIBE
- Cl₂/Ar-Process
- Rotating substrate with adjustable tilt
- Ion source: 15 cm, 13.56 MHz driven
- Ion Optics: Low Divergence
- Beam Neutralisation: filamentfree PBN



Ionfab 300 Plus